
Effect of Growth Temperature and Annealing on ZnO p. 207

Quantum Efficiency Modeling of Amorphous/Crystalline Silicon Heterojunction Photovoltaic Devices p. 213

A Single Source Approach to Deposition of Nickel and Palladium Sulfide Thin Films by LP-MOCVD p. 219

Screen Printable Doped Self-Aligned Metallization for Solar Cells p. 225

Photosensitive Amorphous Si Thin Films Prepared by Magnetron Technology p. 231

Deposition of II/VI Thin Films from Novel Single-Source Precursors p. 237

Amorphous-Microcrystalline Silicon Films Obtained Using Hydrogen Dilution in a DC Saddle-Field Glow-Discharge p. 243

The Role of Hydrogen in Laser Crystallized Polycrystalline Silicon p. 249

The Energy Band Structures of Cd[subscript 1-x]Zn[subscript x] Te Polycrystalline Thin Films and Their Applications for Photovoltaic Devices p. 255

Tunnel Currents in the Photo-Field Detectors and the Auger Transistor under Strong Electric Field p. 259

A Boron Doped Amorphous Silicon Thin-Film Bolometer for Long Wavelength Detection p. 265

Characterization of Sputter Deposited PbTe on Si (111) for Optoelectronic Applications p. 271

Far-Infrared Magnetooptical Generalized Ellipsometry Determination of Free-Carrier Parameters in Semiconductor Thin Film Structures p. 277

Far-Infrared Dielectric Function and Phonon Modes of Spontaneously Ordered (Al[subscript x]Ga[subscript 0.52]In[subscript 0.48])P Electrodeposition of Cu[subscript 2]Se Thin Films by Electrochemical Atomic Layer Epitaxy (EC-ALE) p. 289


Intersubband Transitions in Proton Irradiated InGaAs/InAlAs Multiple Quantum Wells Grown on Lattice Matched InP Substrate p. 301


Native Point Defect Interactions in ZGP Crystals under Influence of e-Beam Irradiation p. 315


High Gain, Low Threshold Current GaInAsP Based VCSELS for Operation at 1.24 um Novel Resistance Reduction and Phase Changes of Contacts to n-Type InP by Rapid Thermal Annealing p. 331

Design of a 364 nm Electrically Pumped Multi-Quantum Well Continuous Wave Nitride Vertical Cavity Surface Emitting Laser p. 337

DLTS Studies of Defects Produced in n-Type Silicon by Hydrogen Implantation at Low Temperature Nanostructures p. 343

p. 349
Effect of Pressure-Enhanced Single Step Annealing on the Silicon Photoluminescence

Mesoscopic Study of the Electronic Properties of Thin Polymer Films

Lanthanide Doped Cubic Boron Nitride

Growth and Characterization of Epitaxial Films of ZnGeP[subscript 2]

Detectors

Intersubband Transitions in InAs/AlSb Quantum Wells

Far Infrared Spectroscopy of In[subscript 0.53]Ga[subscript 0.47]As Quantum Wells on InP(100)

GaSb-Based Materials for Mid-Infrared Photodiodes Operating in the 0.9-2.55 [mu]m Spectral Range

Thermal Stability in HgCdTe IR Photodiodes

Intersubband Transitions in In[subscript x]Ga[subscript 1-x]As/AlGaAs Multiple Quantum Wells for Long Wavelength Infrared Detection

Spectral Response Modification of Quantum Well Infrared Photodetector by Quantum Well Intermixing

III-Nitride Materials and Devices

Preparation of Optoelectronic Devices Based on AlN/AlGaN Superlattices

Dilute Group III-AsN: Bonding of Nitrogen in GaInAsN and AlGaAsN on GaAs and Realization of Long Wavelength (2.3 [mu]m) GaInAsN QWs on InP

Low Temperature Photoluminescence Studies of Narrow Bandgap GaAsSbN Quantum Wells on GaAs

Interband Transitions in GaInNAs/GaAs Single Quantum Wells

Influence of Low-Energy Electron Beam Irradiation on Defects in Activated Mg-Doped GaN

Electrical Isolation of p-Type GaAsN Epitaxial Layers by Ion Irradiation

The Compositional and Optical Characterizations of InGaAsN Alloy Semiconductor Grown by MOVPE

Author Index

Subject Index

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